



Isolated Synchronous Flyback Controller with Integrated *iCoupler*

Preliminary Technical Data

ADP1071-1/ADP1071-2

FEATURES

Current Mode Controller for flyback topology

ADP1071-1: Programmable LLM or CCM for high V_{IN} applications

ADP1071-2: Forced CCM operation

Programmable slope compensation

Integrated 5 kV isolation with Analog Devices *iCoupler* technology

Wide voltage supply range

Primary V_{DD} : Upto 60 V (ADP1071-2 only)

Secondary V_{DD2} : Upto 36 V

Integrated 1A primary side MOSFET driver for

Integrated 1A secondary side MOSFET driver for synchronous rectification

Integrated error amplifier and < 1% accurate reference voltage

Programmable frequency range: 50 kHz – 600 kHz

Duty cycle clamp limit 85%

Programmable soft start and soft start from pre-charged load

Protection features such as short circuit, output overvoltage, and over temperature protection

Power saving light load mode using MODE pin (ADP1071-1 only)

Cycle-by-cycle input overcurrent protection

Precision enable UVLO with hysteresis

Frequency synchronization

Power Good pin for system flagging

Available in 24-pin SOIC_W package

APPLICATIONS

Isolated DC/DC or AC/DC Power conversion

Telecom, Industrial

Small Cell

PoE Powered Device

Enterprise switches/routers

GENERAL DESCRIPTION

The **ADP1071-1/ADP1071-2**¹ is a PWM current mode fixed frequency synchronous flyback controller designed for isolated DC-to-DC power supplies. Analog Devices, Inc., proprietary *iCoupler* devices are integrated in the **ADP1071-1/ADP1071-2** to eliminate the bulky signal transformers and opto-couplers while reducing system design complexity, cost and component count, and improving overall system reliability. With the integrated isolators and drivers on both the primary and secondary, the **ADP1071-1/ADP1071-2** offers a compact system level design and yields a higher efficiency than a diode rectified flyback converter at heavy loads.

Output regulation is achieved by sensing the output voltage on the secondary side, where the feedback and the PWM signals are transmitted between the primary and secondary through the *iCouplers*.

The **ADP1071-1/ADP1071-2** is offered in the 16L SOIC_W with an isolation voltage rating of 5 kV_{RMS}. The ADP1071-2 is designed for isolated DC-DC applications typically with input voltage less than 36V, and the ADP1071-1 targets high input voltage applications, where the DC input voltage can exceed 60V.

The **ADP1071-1/ADP1071-2** offers features such as input current protection, output over-voltage protection (OVP), under voltage lockout (UVLO), precision enable with adjustable hysteresis, over temperature protection (OTP) and light-load power saving mode (LLM).

¹ Protected by U.S. Patent US 7,075,329 B2.

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TYPICAL APPLICATION CIRCUITS

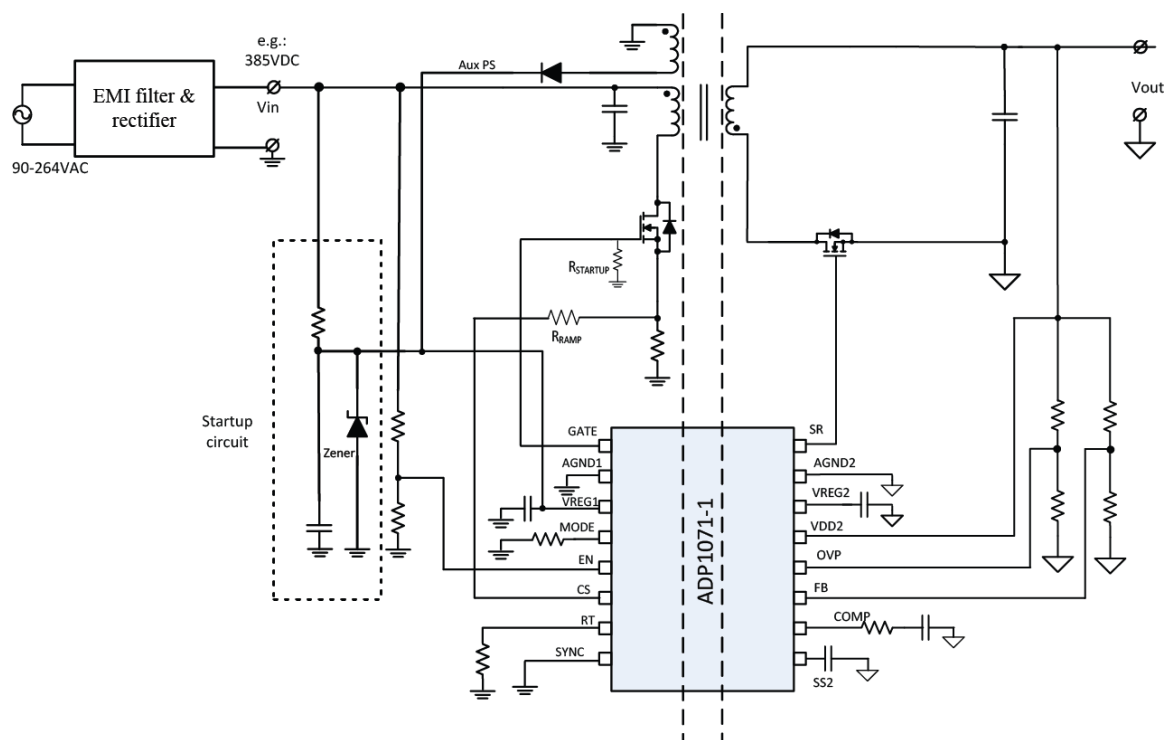


Figure 1. [ADP1071-1](#) Typical Application with External Startup Circuit and Aux Power

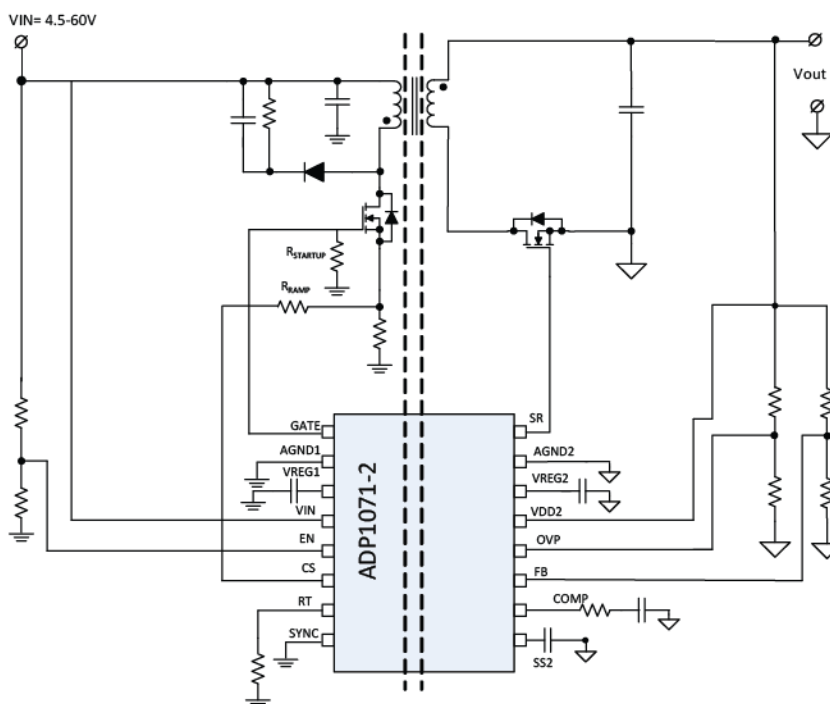


Figure 2. [ADP1071-2](#) Low Input Voltage Flyback Application Circuit

SPECIFICATIONS

$V_{IN} = 24V$, $V_{DD2} = 12V$, $T_A = -40^{\circ}C$ to $+125^{\circ}C$, unless otherwise noted.

Table 1.

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
SUPPLY (primary)						
Supply Voltage	V_{IN}	4.7 μF capacitor from Vin to PGND 1 μF capacitor from VREG1 to PGND	4.7	24	60	V
Quiescent Supply Current	I_{VIN}	$V_{IN} > V_{IN_UVLO}$, GATE pin unloaded At 100kHz At 300kHz At 600kHz		3.8 4.4 6.8		mA mA mA
	I_{VIN}	$V_{IN} > V_{IN_UVLO}$, GATE pin loaded with 2.2nF and 410pF respectively At 100kHz At 300kHz At 600kHz		5.5 11 22		mA mA mA
VIN shutdown current	$I_{VIN_startup}$	$V_{EN} < 1.2V$, VREG1= 0V, VIN= 60 V			35	μA
(VIN + VREG1) startup current		$V_{EN} < 1.2V$, VREG1= 12 V, VIN= 12 V			160	μA
VIN UVLO		VIN rising	4.3	4.5	4.7	V
		VIN falling		4.3 -0.1		V V
UVLO hysteresis		EN>1.2V, 1 μF capacitor on VREG1			1	ms
Time from EN high to GATE output switching		EN<1.0V, 1 μF capacitor on VREG1			1	μs
Time from EN low to GATE output stops switching						
SUPPLY (secondary)						
Supply Voltage	V_{DD2}	4.7 μF capacitor from VDD2 to PGND2 1 μF capacitor from VREG2 to PGND2	4.5	12	36	V
Quiescent supply current	I_{DD2}	SR1 unloaded At 100kHz At 300kHz At 600kHz		6.3 6.4 6.9		mA mA mA
	I_{DD2}	SR loaded with 2.2nF At 100kHz At 300kHz At 600kHz		8 13.5 18		mA mA mA
UVLO threshold		V_{DD2} rising		3.5		V
		V_{DD2} falling		3.45		V
UVLO Hysteresis				50		mV
Secondary UVLO hiccup time				225		ms
OSCILLATOR						
Switching frequency (f_s)		$R_{RT} = 480 k\Omega (\pm 1\%)$ $R_{RT} = 240 k\Omega (\pm 1\%)$ $R_{RT} = 120 k\Omega (\pm 1\%)$ $R_{RT} = 80 k\Omega (\pm 1\%)$ $R_{RT} = 60 k\Omega (\pm 1\%)$ $R_{RT} = 40 k\Omega (\pm 1\%)$	-10% -10% -10% -10% -10% -10%	50 100 200 300 400 600	+10% +10% +10% +10% +10% +10%	kHz kHz kHz kHz kHz kHz
VREG1 pin						
VREG1 voltage clamp		$I_{VREG1} = 3mA$, $V_{EN} < 1.2V$	13.5	14.3	15.2	V
VREG1 clamp series resistance		VREG1 current 5mA and 10mA		16		Ω

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
GATE drivers (primary)						
GATE high voltage		$I_{VREG1} = 20\text{mA}$, $V_{IN} > 9\text{V}$ (ADP1071-2 only)	7.6	8	8.4	V
Gate short circuit peak current ¹		8 V on VREG1		1.0		A
GATE Rise Time		$C_{GATE} = 2.2\text{ nF}$, 10% to 90%		16		ns
GATE Fall Time		$C_{GATE} = 2.2\text{ nF}$, 90% to 10%		16		ns
GATE R_{ON}	R_{ON_SOURCE}	Source 100mA		6		Ω
GATE R_{ON}	R_{ON_SINK}	Sink 100mA		4		Ω
GATE Max Duty Cycle				85		%
GATE minimum on time		At 300 kHz, includes blanking time		150		ns
SR driver (secondary)						
SR high voltage		$I_{VREG2} = 15\text{mA}$, $V_{DD2} > 5.5\text{V}$	4.7	5	5.3	V
SR short circuit peak current ²		5 V on VREG2		1.0		A
SR Rise Time		$C_{SR} = 2.2\text{ nF}$, 10% to 90%		16		ns
SR Fall Time		$C_{SR} = 2.2\text{ nF}$, 90% to 10%		16		ns
SR minimum on time		At 300 kHz		120		ns
SR R_{ON}	$R_{ON_SR_SOURCE}$	Source 100mA		6		Ω
	$R_{ON_SR_SINK}$	Sink 100mA		4	1	Ω
Deadtime Setting GATE to SR		Deadtime between SR falling and GATE rising		25		ns
		Deadtime between GATE falling and SR rising		50		ns
CURRENT LIMIT SENSE (primary)						
CS limit threshold	V_{CS_LIM}	Over current sense limit threshold		120		mV
CS leading edge blanking time				150		ns
Current source di/dt for slope compensation				20		$\mu\text{A}/\text{Ts}$
Current sense amplifier gain			0.5	12	2.5	
Current sense amplifier limit				20		ns
OCF comparator delay				1.25		ms
Time in OCP before entering hiccup mode				45		ms
OCF hiccup time						
FB PIN AND ERROR AMPLIFIER						
Feedback Accuracy Voltage	V_{FB}	$T_j = -40^\circ\text{C}$ to $+85^\circ\text{C}$	-0.85%	+1.2	+0.85%	V
		$T_j = -40^\circ\text{C}$ to $+125^\circ\text{C}$	-1.5%	+1.2	+1.5%	V
FB Input Bias Current			-100	1	+100	nA
Transconductance	gm		212	250	287	μs
Output current clamp minimum				-65		μA
Output current clamp maximum				40		μA
COMP clamp maximum voltage				2.52		V
COMP clamp minimum voltage				0.6		V
Open loop gain				80		dB
Output shunt resistance				50		G Ω
Gain Bandwidth Product				1		MHz
PRECISION ENABLE THRESHOLD						
EN threshold	V_{EN}	EN rising	1.14	1.2	1.26	V
EN hysteresis		$V_{EN} < 1.2\text{ V}$	3	4	5	mA
		$V_{EN} > 1.2\text{ V}$		1		μA
EN Hysteresis current				3		μA

Parameter	Symbol	Test Conditions/Comments	Min	Typ	Max	Unit
LIGHT LOAD MODE LLM current source		ADP1071-1: Resistor from MODE to AGND1	5	6	7	μA
Temperature						
Thermal shutdown				155		°C
Hysteresis				-15		°C
SOFT START						
SS1 time on primary	t_{SS1}	GATE resistor= 10kΩ GATE resistor= 22kΩ GATE resistor= 47kΩ GATE resistor= 100kΩ		16x775 64x775 256x775 4x775		Ts Ts Ts Ts
SS2 current source		During startup	15	20	25	μA
SS2 discharging current		During a fault condition or soft stop		30		μA
SYNC pin						
Synchronization Range			100		600	kHz
Input Pulse Width			100			ns
Number of cycles before synchronization				7		
Input low voltage					0.4	V
Input high voltage			3			V
Leakage Current					1	μA
COMP signal delay through iCoupler				600		ns
iCOUPLER						
Rated Dielectric Insulation Voltage		1 minute duration		5		kV
Minimum External Air Gap (Clearance)		Measured from input terminals to output terminals, shortest distance through air		7.6 min		mm
Minimum External Air Gap (Creepage)		Measured from input terminals to output terminals, shortest distance path along body		7.6 min		mm
Minimum Internal Gap (Internal Clearance)		Insulation distance through insulation		0.030 >400		mm V
Tracking Resistance (Comparative Tracking Index)	CTI	Material Group (DIN VDE 0110, 1/89, Table		II		
Isolation Group			-25		25	kV/μs
Common mode Transient Immunity, Dynamic						
FB AND OVPTHRESHOLDS						
OV Hysteresis		Over-voltage threshold for OVP pin	1.3	1.36	1.42	V
UV threshold		Under-voltage threshold	1.04	1.11	1.16	mV V
FB pin UV Hysteresis				25		mV
OVP comparator delay (includes iCoupler delay)				250		ns
OVP pin leakage current				1		μA
OVP hiccup		Time before entering OVP hiccup mode		200		ms
		Hiccup time triggered by OVP event		200		ms

¹ Short-circuit duration less than 1 μs. Average power must conform to the limit shown under the Absolute Maximum Ratings.

² Short-circuit duration less than 1 μs. Average power must conform to the limit shown under the Absolute Maximum Ratings.

REGULATORY INFORMATION

See Table 5 and the Insulation Lifetime section for details regarding recommended maximum working voltages for specific cross-isolation waveforms and insulation levels.

Table 2.

UL (Pending)	CSA (Pending)	VDE (Pending)	CQC (Pending)
Recognized Under UL 1577 Component Recognition Program ¹ Single Protection, 5000 V rms Isolation Voltage	Approved under CSA Component Acceptance Notice 5A CSA 60950-1-07+A1+A2 and IEC 60950-1, second edition, +A1+A2: Basic insulation at 780 V rms (1103 V peak) Reinforced insulation at 390 V rms (552 V peak) IEC 60601-1 Edition 3.1: Basic insulation (1 means of patient protection (1 MOPP)), 490 V rms (686 V peak) Reinforced insulation (2 MOPP), 238 V rms (325 V peak) CSA 61010-1-12 and IEC 61010-1 third edition: Basic insulation at 300 V rms mains, 780 V secondary (1103 V peak)	Certified according to DIN V VDE V 0884-10 (VDE V 0884-10):2006-12 ² Reinforced insulation, $V_{IORM} = 849$ peak, $V_{IOTM} = 8000$ V peak	Certified by CQC11-471543-2012, GB4943.1-2011: Basic insulation at 780 V rms (1103 V peak) Reinforced insulation at 389 V rms (552 V peak), tropical climate, altitude ≤ 5000 meters
File E214100	File 205078	File 2471900-4880-0001	File (pending)

¹ In accordance with UL 1577, each product is proof tested by applying an insulation test voltage ≥ 6000 V rms for 1 sec.

² In accordance with DIN V VDE V 0884-10, each product is proof tested by applying an insulation test voltage ≥ 1592 V peak for 1 sec (partial discharge detection limit = 5 pC). The * marking branded on the component designates DIN V VDE V 0884-10 approval.

ABSOLUTE MAXIMUM RATINGS

Table 3.

Parameter	Rating
VIN, EN	66 V
VDD2	42 V
VREG1	16V
GATE	-0.3V to 16V
RT, CS, SYNC, SS2, FB, COMP, OVP, MODE, SR, VREG2	+6.0V
AGND1, AGND2	±0.3 V
Operating Temperature Range	−40°C to +125°C
Common mode Transients ¹	±25 kV/μs
Junction Temperature	150°C
Peak Solder Reflow Temperature	
SnPb Assemblies (10 sec to 30 sec)	240°C
RoHS-Compliant Assemblies (20 sec to 40 sec)	260°C
ESD	
Charged Device Model	250 V
Human Body Model	1 kV

¹ Refers to common mode transients across the insulation barrier. Common mode transients exceeding the absolute maximum rating can cause latch up or permanent damage.

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

THERMAL RESISTANCE

θ_{JA} is specified for the worst-case conditions, that is, a device soldered in a circuit board for surface-mount packages. JEDEC thermal resistance values (θ_{JA} & θ_{JC}) and thermal characterization parameter (Ψ_{JT}) shown in Table 4 should be used in compliance with JEDEC standards for thermal reporting (JESD51-12).

Table 4. Thermal Resistance

Package Type	θ_{JA}	θ_{JC}	Ψ_{JT}
SOIC_W 16-Lead	79.3 °C/W	44.6 °C/W	9.7 °C/W

Table 5. Maximum Continuous Working Voltage¹

Parameter	Max	Unit	Constraint
WAVEFORM			
AC Voltage			
Bipolar	560	V peak	50-year minimum lifetime
Unipolar	1131	V peak	50-year minimum lifetime
DC Voltage	1131	V peak	50-year minimum lifetime

¹ Refers to continuous voltage magnitude imposed across the isolation barrier. See the Insulation Lifetime section for more details.

ESD CAUTION



ESD (electrostatic discharge) sensitive device.

Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

PIN CONFIGURATIONS AND FUNCTION DESCRIPTIONS

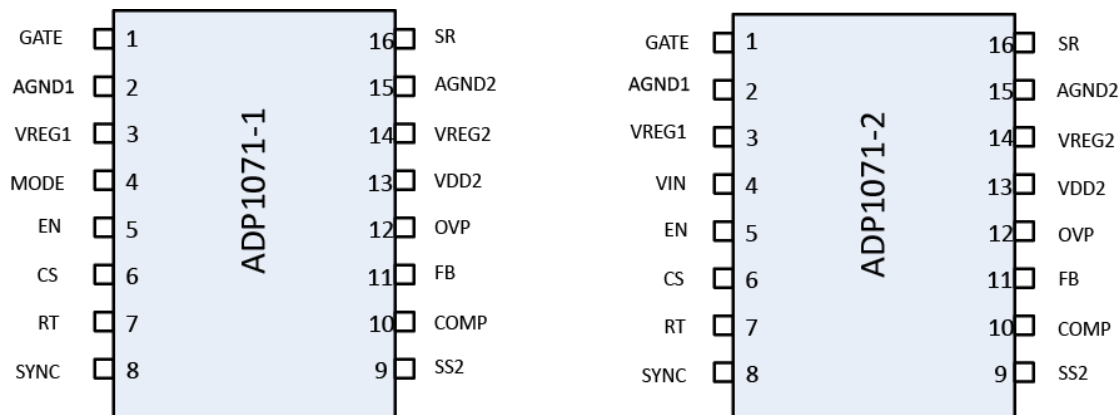


Figure 3. Pin Configuration

Table 6. Pin Function Descriptions

Pin	ADP1071-1	ADP1071-2	Description
1	GATE	GATE	Driver output for main power MOSFET on the primary side. Multiple function pin. Connect a resistor from GATE to AGND1 to setup the open loop soft start time.
2	AGND1	AGND1	Ground for primary
3	VREG1	VREG1	8V regulated LDO output for the MOSFET driver. Connect 1uF or greater from VREG1 to AGND1.
4	MODE	-	ADP1071-1 only: Connect MODE to GND to enable forced continuous conduction mode (CCM), or to a high logic (2.5V or higher) to force a LLM operation, or to a resistor to setup a fixed light load mode (LLM) threshold voltage.
4	-	VIN	ADP1071-2 only: Input voltage. See input voltage section. Connect a 4.7uF capacitor at this pin. The size of this capacitor can be reduced if the input voltage to this pin is guaranteed to be stable. This pin is referenced to AGND1.
5	EN	EN	Precision enable input. The controller is enabled when EN is above the EN threshold voltage. This pin also has a programmable EN hysteresis. This pin is referenced to AGND1.
6	CS	CS	Input current sensing. This pin senses the input pulse width modulated current. Place a current sense resistor between the source terminal of the power MOSFET and PGND1. This current sense resistor sets up the input current limit. This pin is also used for external slope compensator. Connect a resistor from CS to the current sense resistor to generate a voltage ramp for the slope compensation. This pin is referenced to AGND1. It is recommended to connect a 33-100pF capacitor at this pin which acts as an RC filter along with the slope compensation resistor.
7	RT	RT	Connect a resistor from RT to AGND1 to set the oscillator frequency.
8	SYNC	SYNC	Connect an external clock to the SYNC pin to synchronize the internal oscillator to this external clock frequency. Connect SYNC to AGND1 if this feature is not used. It is recommended that the SYNC frequency be within 10% of the frequency set by the RT pin.
9	SS2	SS2	Soft start on secondary. Connect a capacitor from SS2 to AGND2 to setup the soft start time on the secondary.
10	COMP	COMP	Compensation node on the secondary. This pin is the output of the gm amplifier. This pin is referenced to AGND2.
11	FB	FB	Feedback node on the secondary. Set up the resistor divider from the output voltage such that the nominal voltage when the power supply is in regulation is 1.2 Volts. This pin is referenced to AGND2.
12	OVP	OVP	Output overvoltage protection (OVP). The OVP threshold is set at 1.36 Volts. Connect a resistive divider from OVP to the output and AGND2.
13	VDD2	VDD2	Input supply on the secondary. Connect VDD2 to the output voltage for a self-driven configuration. Connect a 4.7uF capacitor from this pin to AGND2. The size of this capacitor can be reduced if the input voltage to this pin is guaranteed to be stable.
14	VREG2	VREG2	5V regulated LDO output for internal bias and powering the drivers of the synchronous rectifiers. Do not use this pin as a reference or load this pin in any way. Connect a 1uF capacitor from this pin to AGND2.
15	AGND2	AGND2	Analog ground on secondary.
16	SR	SR	Driver output for synchronous rectifier MOSFET.

SIMPLIFIED BLOCK DIAGRAM

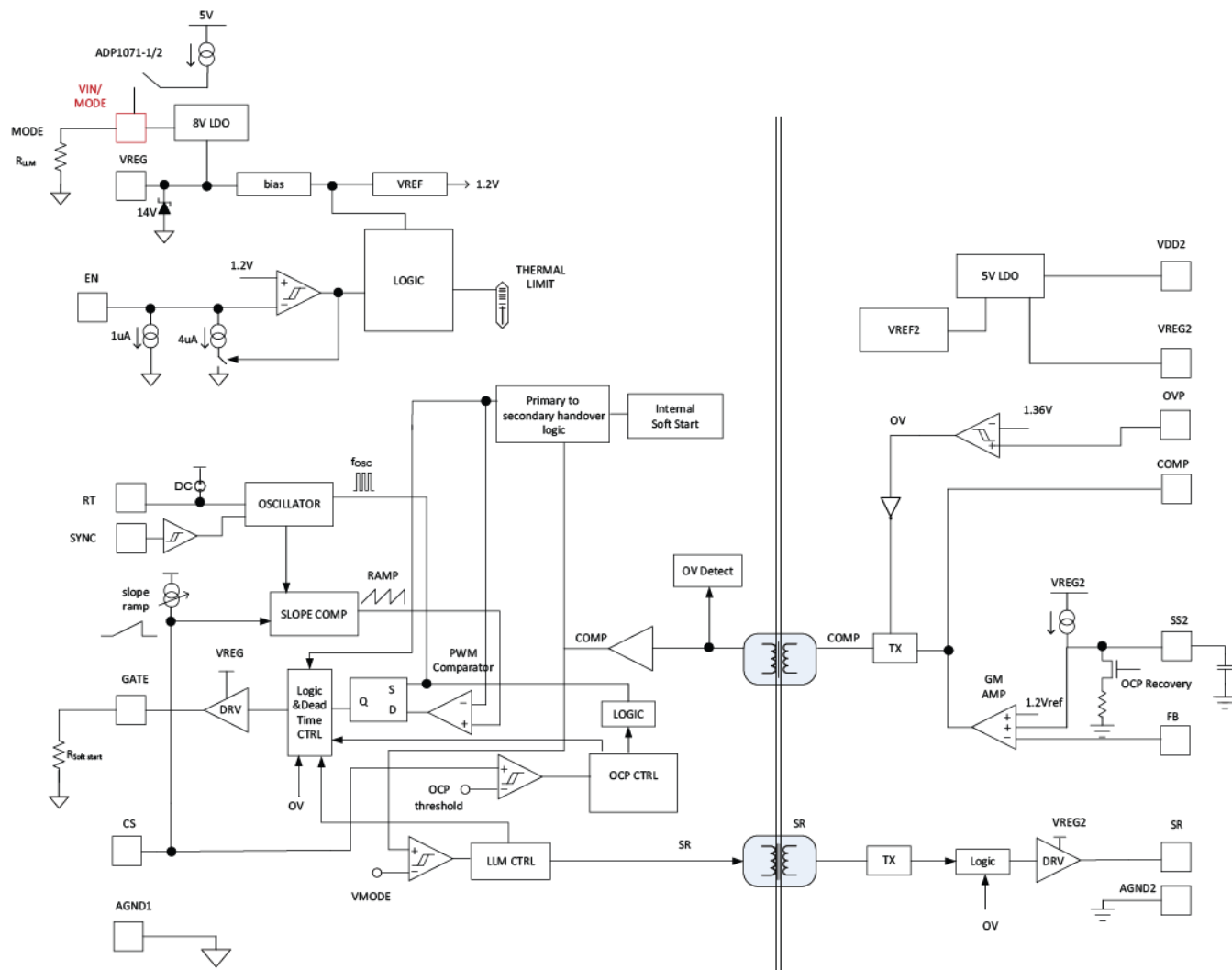


Figure 4. Simplified Block Diagram

APPLICATIONS INFORMATION

INSULATION LIFETIME

All insulation structures eventually break down when subjected to voltage stress over a sufficiently long period. The rate of insulation degradation is dependent on the characteristics of the voltage waveform applied across the insulation. In addition to the testing performed by the regulatory agencies, Analog Devices carries out an extensive set of evaluations to determine the lifetime of the insulation structure within the [ADP1071-1/ADP1071-2](#).

Analog Devices performs accelerated life testing using voltage levels higher than the rated continuous working voltage. Acceleration factors for several operating conditions are determined. These factors allow calculation of the time to failure at the actual working voltage.

The values shown in Table 5 summarize the peak voltage for 50 years of service life for a bipolar ac operating condition. In many cases, the approved working voltage is higher than the 50-year service life voltage. Operation at these high working voltages can lead to shortened insulation life in some cases.

The [ADP1071-1/ADP1071-2](#) insulation lifetime depends on the voltage waveform type imposed across the isolation barrier. The *iCoupler* insulation structure degrades at different rates depending on whether the waveform is bipolar ac, unipolar ac, or dc. Figure 5, Figure 6, and Figure 7 illustrate these different isolation voltage waveforms.

A bipolar ac voltage environment is the worst case for the *iCoupler* products yet meets the 50-year operating lifetime recommended by Analog Devices for maximum working voltage. In the case of unipolar ac or dc voltage, the stress on the insulation is sig-

nificantly lower. This allows operation at higher working voltages while still achieving a 50-year service life. Treat any cross-insulation voltage waveform that does not conform to Figure 6 or Figure 7 as a bipolar ac waveform, and limit its peak voltage to the 50-year lifetime voltage value listed in Table 5.

Note that the voltage presented in Figure 6 is shown as sinusoidal for illustration purposes only. It is meant to represent any voltage waveform varying between 0 V and some limiting value. The limiting value can be positive or negative, but the voltage cannot cross 0 V.

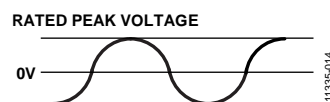


Figure 5. Bipolar AC Waveform

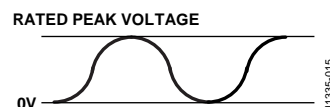


Figure 6. Unipolar AC Waveform

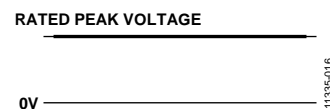
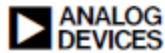
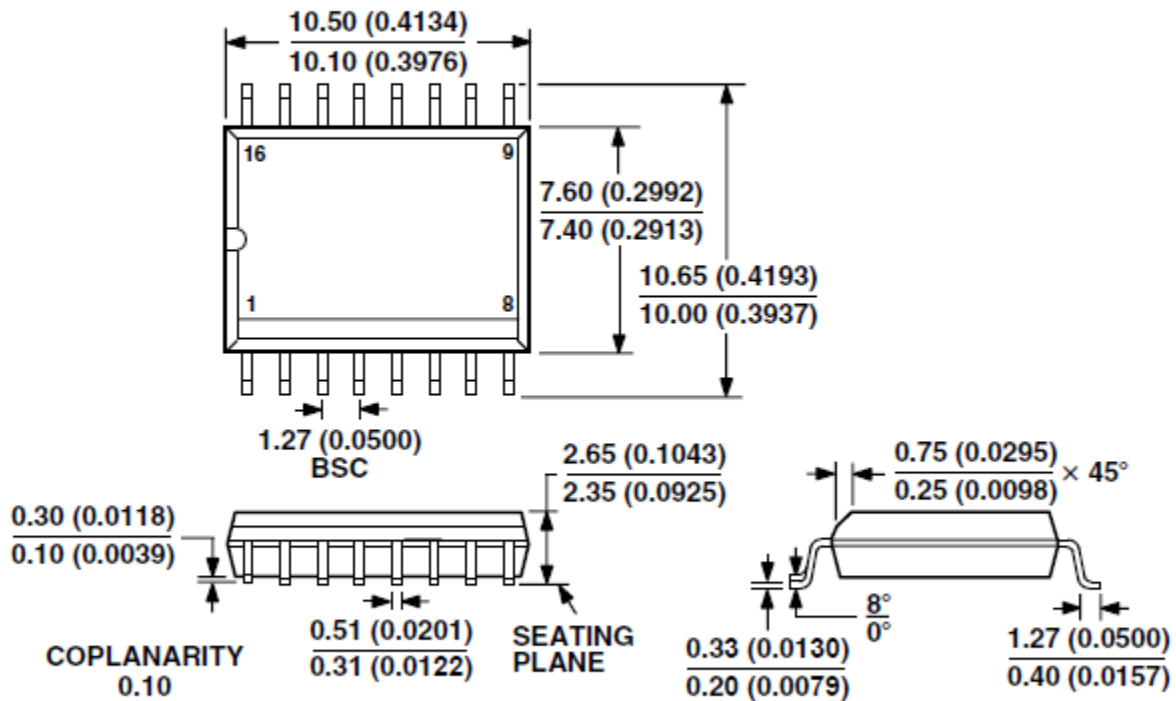


Figure 7. DC Waveform

OUTLINE DIMENSIONS



16-Lead Standard Small Outline Package [SOIC]
Wide Body
(RW-16)
Dimensions shown in millimeters and (Inches)



COMPLIANT TO JEDEC STANDARDS MS-013AA
CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS
(IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR
REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN

Figure 8. 16-Lead SOIC Wide Body Package